



DMN53D0L

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
50V	1.6Ω @ V _{GS} = 10V	500 mA
50 V	2.5Ω @ V_{GS} = $4.5V$	200 mA

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Mechanical Data

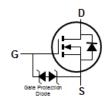
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)





Top View

G S



Top View

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN53D0L-7	SOT23	3000/Tape & Reel
DMN53D0L-13	SOT23	10000/Tape & Reel

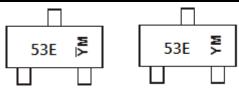
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Shanghai A/T Site

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site

53E = Product Type Marking Code

 \underline{YM} = Date Code Marking for SAT (Shanghai Assembly/ Test site) \underline{YM} = Date Code Marking for CAT (Chengdu Assembly/ Test site) \underline{Y} or \underline{Y} = Year (ex: B = 2014)

M = Month (ex: 9 = September)

Date Code Kev

Date Code Itt	<u> </u>											
Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D			F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current (Note 6)	Ι _D	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	370	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	344	°C/W
Total Power Dissipation (Note 6)	P _D	540	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	236	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

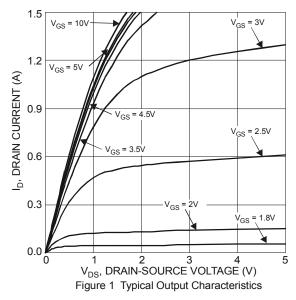
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

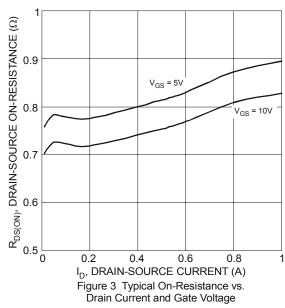
	,		r		r	r		
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	50	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	V _{DS} = 50V, V _{GS} = 0V		
Gate-Body Leakage	I _{GSS}	_	_	10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(th)}	0.8	_	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		
		_	_	1.6		$V_{GS} = 10V, I_D = 500mA$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	2.5	Ω	$V_{GS} = 4.5V, I_D = 200mA$		
		_	_	4.5		$V_{GS} = 2.5V, I_D = 100mA$		
Source-Drain Diode Forward Voltage	V _{SD}	_	_	1.4	V	V _{GS} = 0V, I _S = 500mA		
DYNAMIC CHARACTERISTICS (Note 8)				÷	-			
Input Capacitance	C _{iss}	_	46	_	pF			
Output Capacitance	Coss	_	5.3		pF	V _{DS} = 25V, V _{GS} = 0V -f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	4.0		pF			
Total Gate Charge	Qg	_	0.6	_	nC	4.5)(.)(
Gate-Source Charge	Q _{gs}	_	0.2		nC	$V_{GS} = 4.5V, V_{DS} = 10V,$		
Gate-Drain Charge	Q_{gd}	_	0.1		nC	I _D = 250mA		
Turn-On Delay Time	t _{D(on)}	_	2.7	_	ns			
Turn-On Rise Time	t _r		2.5		ns	V _{DD} = 30V, V _{GS} = 10V,		
Turn-Off Delay Time	t _{D(off)}	_	19	_	ns	$R_G = 25\Omega$, $I_D = 200 \text{mA}$		
Turn-Off Fall Time	t _f		11		ns			

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







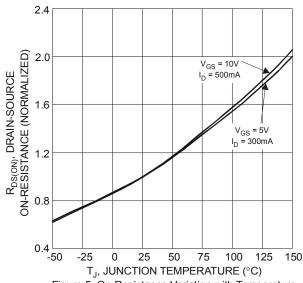
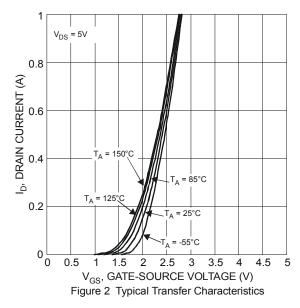
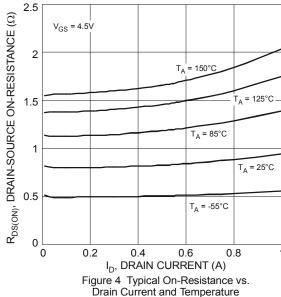


Figure 5 On-Resistance Variation with Temperature





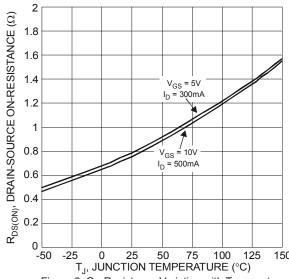


Figure 6 On-Resistance Variation with Temperature



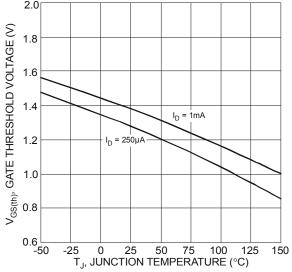
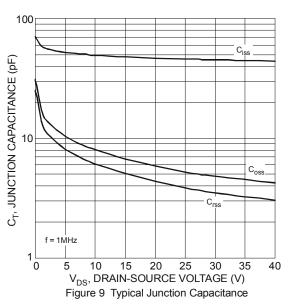
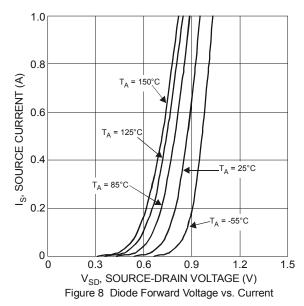
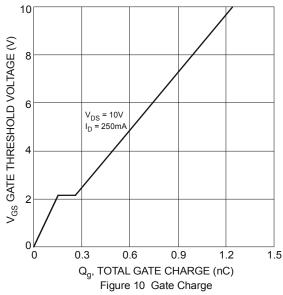


Figure 7 Gate Threshold Variation vs. Ambient Temperature

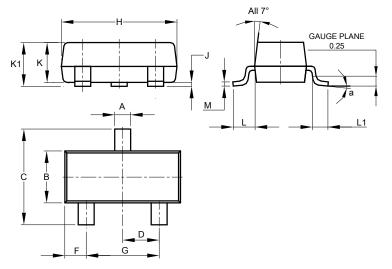






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

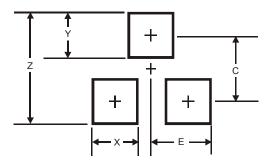


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	α 8°						
All	All Dimensions in mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35

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